

Silicon NPN Power Transistors

2SC1111

DESCRIPTION

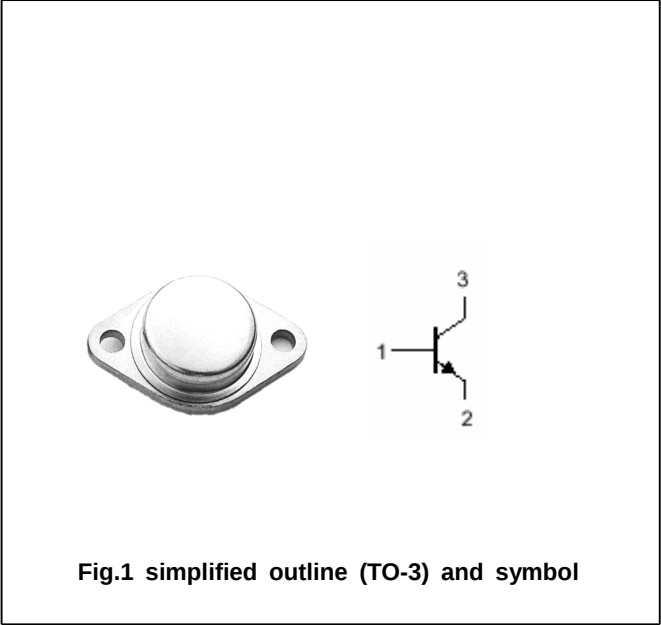
- With TO-3 package
- Wide area of safe operation

APPLICATIONS

- For audio frequency power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=?)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	140	V
V _{CEO}	Collector-emitter voltage	Open base	80	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		6	A
P _C	Collector power dissipation	T _C =25°	50	W
T _J	Junction temperature		150	°
T _{stg}	Storage temperature		-55~150	°

Silicon NPN Power Transistors**2SC1111****CHARACTERISTICS**T_j=25° unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA ; I _B =0	80			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =0.5A			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =140V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =3A ; V _{CE} =4V	30		150	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =12V		10		MHz
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =10V, f=1MHz	115			pF

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PACKAGE OUTLINE

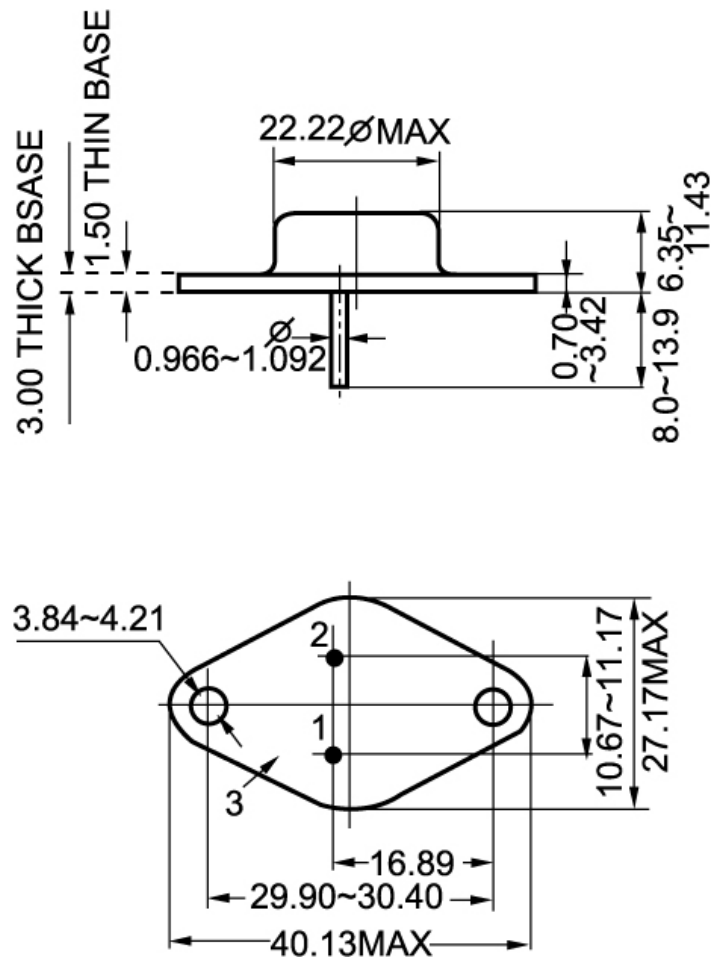


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)